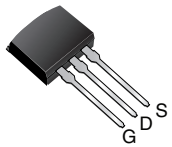


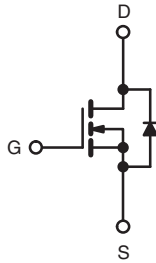
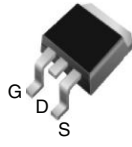
Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	500
$R_{DS(on)}$ (Max.) (Ω)	$V_{GS} = 10\text{ V}$ 3.0
Q_g (Max.) (nC)	17
Q_{gs} (nC)	4.3
Q_{gd} (nC)	8.5
Configuration	Single

I²PAK (TO-262)



D²PAK (TO-263)



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{OSS} specified
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

TYPICAL SMPS TOPOLOGIES

- Two Transistor Forward
- Half Bridge and Full Bridge

ORDERING INFORMATION		
Package	D ² PAK (TO-263)	I ² PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHF820AS-GE3	SiHF820AL-GE3
Lead (Pb)-free	IRF820ASPbF	IRF820ALPbF
	SiHF820AS-E3	SiHF820AL-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	500	V	
Gate-Source Voltage		V_{GS}	± 30		
Continuous Drain Current	V_{GS} at 10 V	I_D	$T_C = 25\text{ }^\circ\text{C}$	2.5	A
			$T_C = 100\text{ }^\circ\text{C}$	1.6	
Pulsed Drain Current ^{a, e}		I_{DM}	10		
Linear Derating Factor			0.4	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy ^{b, e}		E_{AS}	140	mJ	
Avalanche Current ^a		I_{AR}	2.5	A	
Repetitive Avalanche Energy ^a		E_{AR}	5.0	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	50	W	
Peak Diode Recovery dV/dt ^{c, e}		dV/dt	3.4	V/ns	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d		
Mounting Torque	6-32 or M3 screw		10		lbf · in
			1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 45\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 2.5\text{ A}$ (see fig. 12).
- $I_{SD} \leq 2.5\text{ A}$, $dI/dt \leq 270\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.
- Uses IRF820A, SiHF820A data and test conditions.

* Pb containing terminations are not RoHS compliant, exemptions may apply

IRF820AS, SiHF820AS, IRF820AL, SiHF820AL




Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mounted, steady-state) ^a	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	2.5	

Note

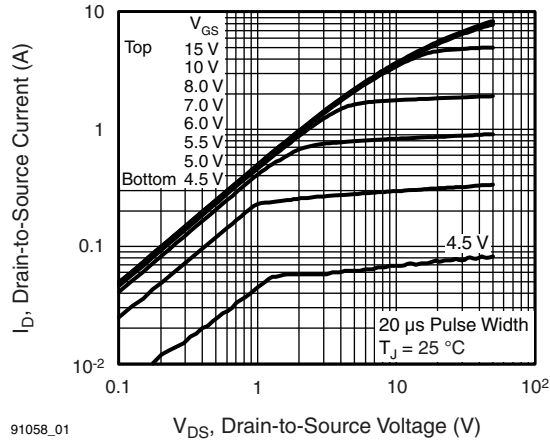
a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	500	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}^d$	-	0.60	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.5	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ $I_D = 1.5\text{ A}^b$	-	-	3.0	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 1.5\text{ A}^d$	1.4	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5 ^d	-	340	-	pF	
Output Capacitance	C_{oss}		-	53	-		
Reverse Transfer Capacitance	C_{rss}		-	2.7	-		
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	490	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$	-	15	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 2.5\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^{b, d}	-	-	17	nC
Gate-Source Charge	Q_{gs}			-	-	4.3	
Gate-Drain Charge	Q_{gd}			-	-	8.5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 2.5\text{ A}, R_g = 21\text{ }\Omega, R_D = 97\text{ }\Omega$, see fig. 10 ^{b, d}	-	8.1	-	ns	
Rise Time	t_r		-	12	-		
Turn-Off Delay Time	$t_{d(off)}$		-	16	-		
Fall Time	t_f		-	13	-		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	2.5	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	10		
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 2.5\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.6	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 2.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b, d$	-	330	500	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	760	1140	nC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

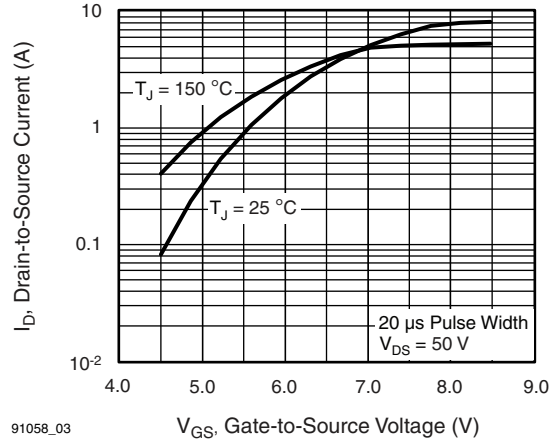
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
- Uses IRF820A/SiHF820A data and test conditions.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



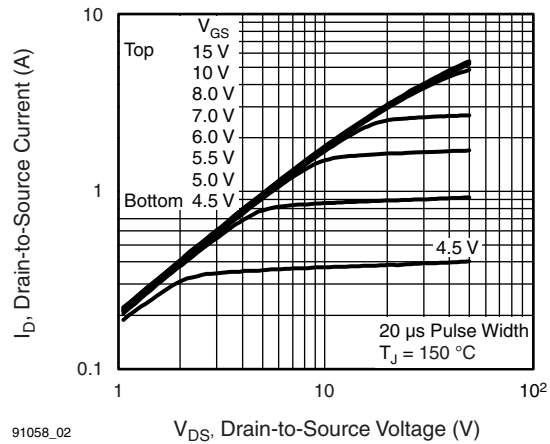
91058_01

Fig. 1 - Typical Output Characteristics



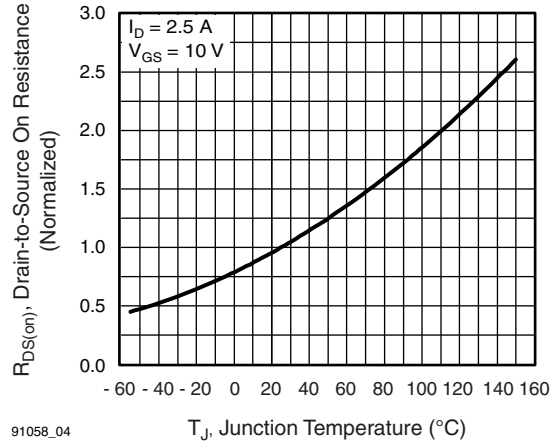
91058_03

Fig. 3 - Typical Transfer Characteristics



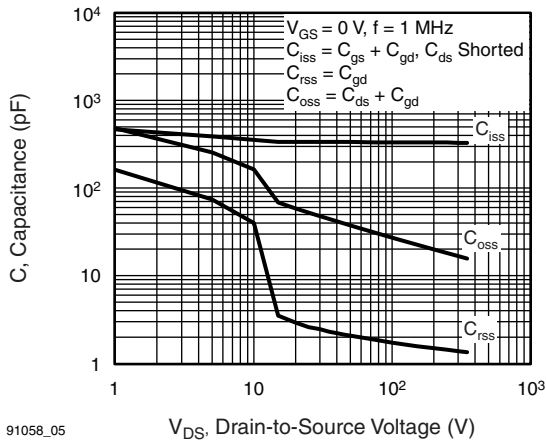
91058_02

Fig. 2 - Typical Output Characteristics



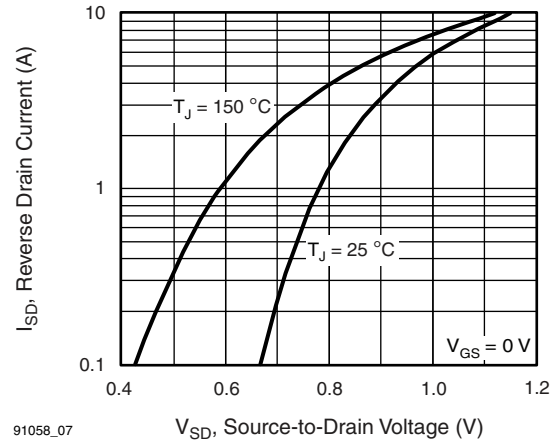
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Fig. 4 - Normalized On-Resistance vs. Temperature



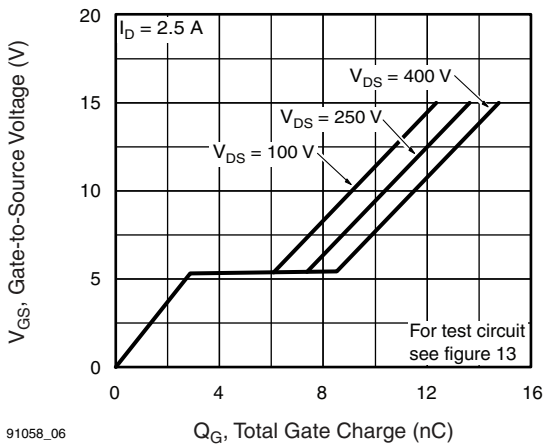
91058_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



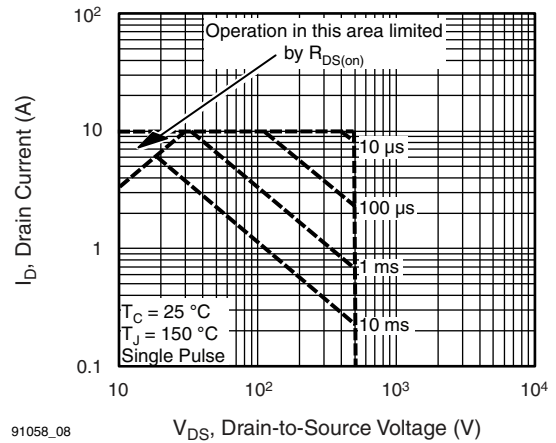
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91058_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91058_08

Fig. 8 - Maximum Safe Operating Area

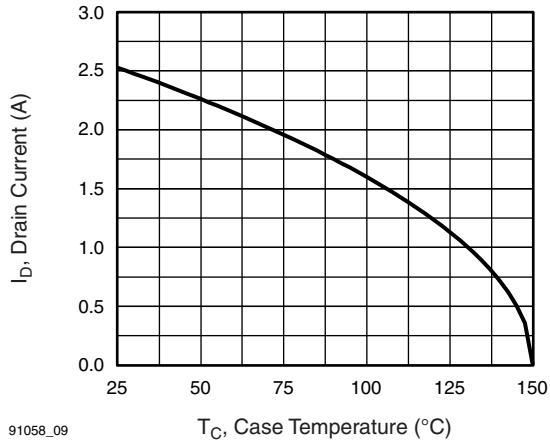


Fig. 9 - Maximum Drain Current vs. Case Temperature

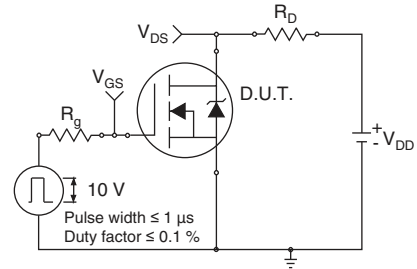


Fig. 10a - Switching Time Test Circuit

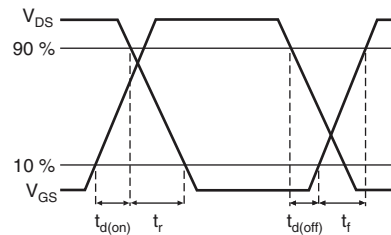


Fig. 10b - Switching Time Waveforms

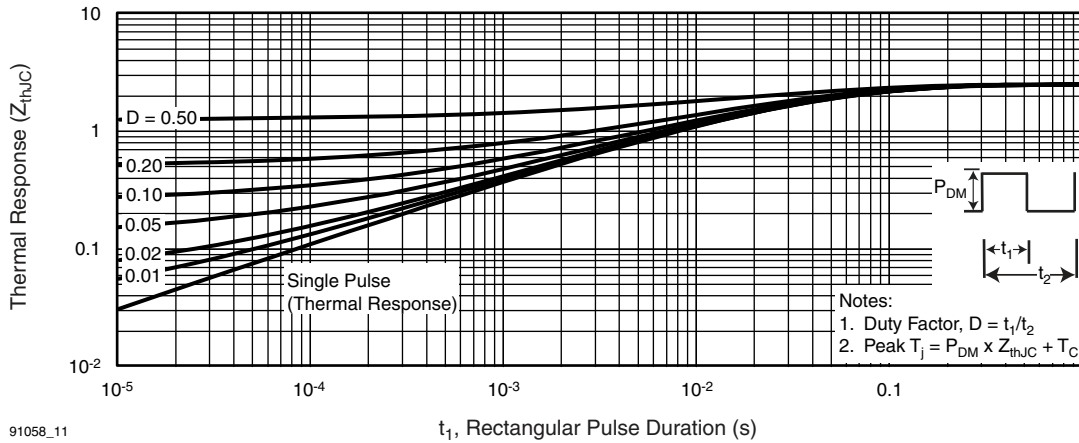


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

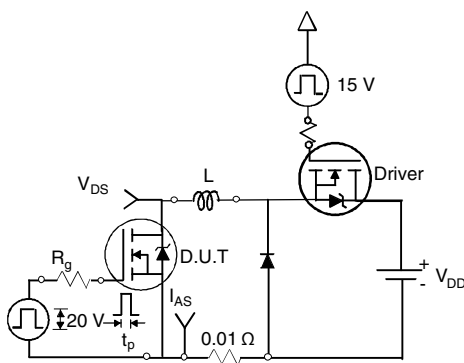


Fig. 12a - Unclamped Inductive Test Circuit

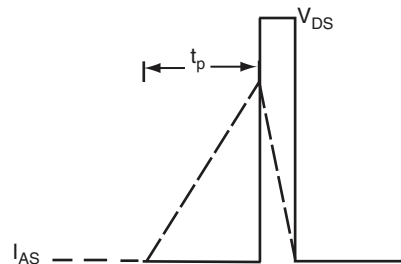


Fig. 12b - Unclamped Inductive Waveforms

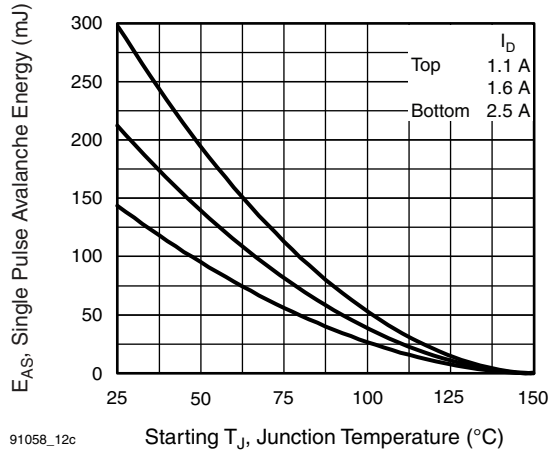


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

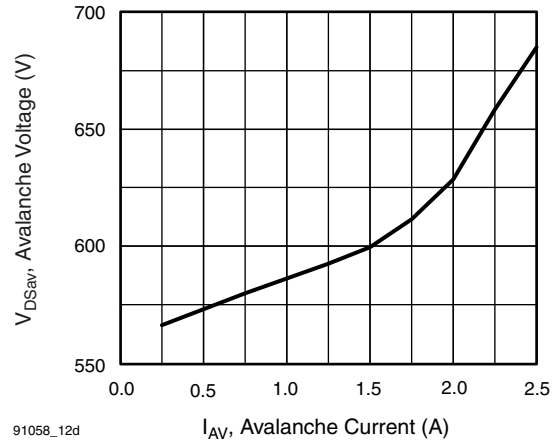


Fig. 12d - Basic Gate Charge Waveform

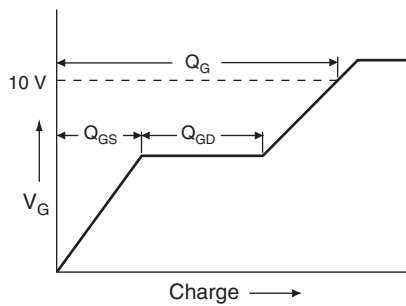


Fig. 13a - Maximum Avalanche Energy vs. Drain Current



Fig. 13b - Gate Charge Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



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